Form PTO-1449 Sheet 1 of 2

Applicant: Ryuzo Iga et al. Confirmation No.: 9935
Serial No.: 10/577,626
April 28, 2006
Confirmation No.: 9935
Att'y Docket No.: 14321.84
Art Unit: 2828

For: SEMICONDUCTOR OPTICAL DEVICE AND A METHOD OF FABRICATING THE SAME

INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANT

U.S. Patent Documents

Examiner <u>Initial*</u>	Document Number	Issue <u>Date</u>	<u>Name</u>
1	5,470,785	11/28/1995	Kondo
2	6,300,153 B1	10/09/2001	Koui
3	2001/0030327 A1	10/18/2001	Furushima
4	2003/0067010 A1	04/10/2003	Iga et al.
5	2004/0057483 A1	03/25/2004	Takemi et al.

Foreign Patent Documents

Examiner	Document	Publication	Country or	m 1.º
<u>Initial</u> *	<u>Number</u>	Date	Patent Office	<u>Translation</u>
6	61-180493	08/13/1986	Japan	Partial
7	3-53582	03/07/1991	Japan	Partial
8	05-021891	01/29/1993	Japan	No
9	05-102607	04/23/1993	Japan	No
10	06-177482	06/24/1994	Japan	No
11	06-283816	10/07/1994	Japan	No
12	07-162091	06/23/1995	Japan	No
13	07-202317	08/04/1995	Japan	No
14	09-283846	10/31/1997	Japan	No
15	2000-260714	09/22/2000	Japan	No
16	2001-298240	01/26/2001	Japan	No
17	2003-60311	02/28/2003	Japan	No
18	2004-119467	04/15/2004	Japan	No

Examiner: Date Considered:

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Form PTO-1449 Sheet 2 of 2

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	Other Documents
	(including author, title, pertinent pages, etc.)
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19	A. Dadgar et al., <i>Ruthenium: A Superior Compensator of InP</i> , Applied Physics Letters, Vol. 73, No. 26, December 28, 1998, pp. 3878-3880.
20	A. van Geelen et al., <i>Ruthenium Doped High Power 1.48 μm SIPBH Laser</i> , 11 th International Conference on Indium Phosphide and Related Materials, Davos, Switzerland, May 16-20, 1999, TuB 1-2, pp. 203-206.
21	Ryuzo Iga et al., <i>Ruthenium-Doped InP Buried 1.3 µm DFB Lasers on a P-Type Substrate</i> , 2004 International Conference on Indium Phoshide and Related Materials, Conference Proceedings, 16 th IPRM, Kagoshima, Japan, May 31-June 4, 2004, pp. 742-745.
22	Ryuzo Iga et al., <i>Directly Modulated 1.3 µm DFB Lasers with a Buried Heterostructure Using Ru-doped Semi-Insulating InP</i> , Technical Report of IEICE, EMD2004-43, CPM2004-69, OPE2004-126, LQE2004-41(2004-08), pp. 19-24 (only Abstract is attached).
23	Ryuzo Iga et al., Directly Modulated 1.3-um DFB Laser with a Buried Structure Formed by

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Using Ru-doped Semi-insulating InP, 31p-ZH-10, 2005 (all the document is translated).

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Examiners will consider all citations submitted in conformance with 37 C.F.R. § 1.98 and MPEP Sec. 609 and place their initials adjacent the citations in the spaces provided on this form. Examiners will also initial citations not in conformance with the guidelines which may have been considered. A reference may be considered by the Examiner for any reason whether or not the citation is in full conformance with the guidelines. A line will be drawn through a citation if it is not in conformance with the guidelines AND has not been considered. A copy of the submitted form, as reviewed by the Examiner, will be returned to the applicant with the next communication. The original of the form will be entered into the application file.

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The reference designations "A1," "A2," etc. (referring to Applicant's reference 1, Applicant's reference 2, etc.) will be used by the Examiner in the same manner as Examiner's reference designations "A," "B," "C," etc. on Office Action Form PTO-1142.

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